

WHAT IS CLAIMED IS:

1. A method of making a transparent article comprising:

providing a transparent, non-metallic substrate; and

5 depositing upon the substrate, in sequence, a first dielectric film, a metal film, a second dielectric film of a metal oxide, and a protective film of silicon nitride having a thickness in the range of 10 to 150 Å.

2. The method of claim 1 wherein the second dielectric film has an index of refraction essentially the same as that of silicon nitride.

10 3. The method of claim 2 wherein said second dielectric film and the silicon nitride film are contiguous.

4. The method of claim 1 wherein the combined thickness of said second dielectric film and the silicon nitride protective film ranges from about 250 to 400 Å.

15 5. The method of claim 4 wherein the combined thickness of said second dielectric film and said silicon nitride film is 300-350 Å.

6. The method of claim 5 wherein the combined thickness of said second dielectric film and said silicon nitride film is 275-325 Å.

7. The method of claim 1 wherein the metal film is silver.

8. The method of claim 7, wherein the metal film of silver is 70 - 100 Å.

20 9. The method of claim 1 wherein said metal oxide is zinc oxide or titanium dioxide.

10. The method of claim 1, wherein the metal film is 70 – 100 Å.

11. A method of making a transparent article comprising:

providing a transparent, non-metallic substrate; and

depositing upon the substrate, in sequence, a dielectric film contiguous to the transparent substrate, a metal film, a shielding film contiguous to the metal film, a metal oxide film, and a protective film of from 10Å to 150 Å of silicon nitride contiguous to said metal oxide film.

5 12. The method of claim 11 wherein the metal film is silver.

 13. The method of claim 12, wherein the metal film of silver is 70 - 100 Å.

 14. The method of claim 11 wherein the index of refraction of the metal oxide film is essentially the same as silicon nitride.

 15. The method of claim 11 wherein the shielding film and the metal oxide film are
10 contiguous.

 16. The method of claim 11 wherein the metal oxide film is zinc oxide or titanium dioxide.

 17. The method of claim 11, wherein the metal film is 70 - 100 Å.

 18. The method of claim 11 wherein the combined thickness of said second dielectric
15 film and the silicon nitride protective film ranges from about 250 to 400 Å.